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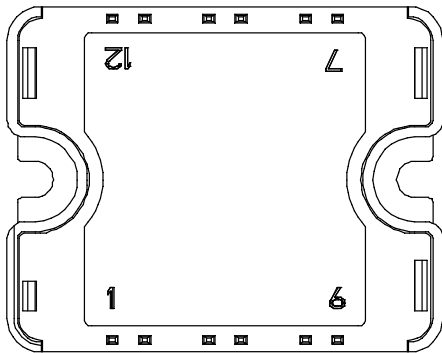
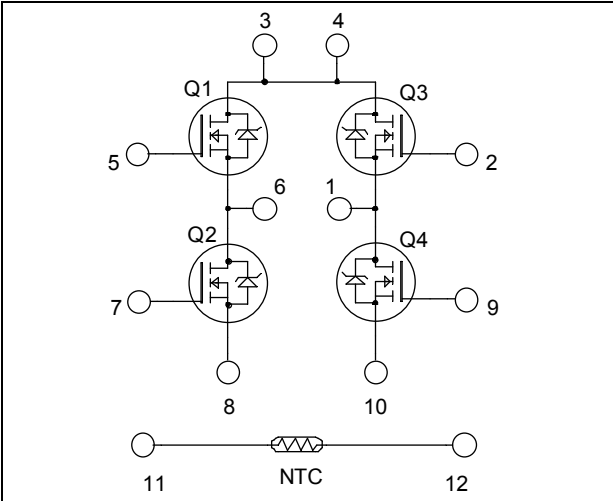
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Full - Bridge MOSFET Power Module

$V_{DSS} = 1200V$
 $R_{DSon} = 1.4\Omega \text{ typ @ } T_j = 25^\circ C$
 $I_D = 8A \text{ @ } T_c = 25^\circ C$



Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 8™ Fast FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	8
		$T_c = 80^\circ C$	6
I_{DM}	Pulsed Drain current	50	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	1.68	Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	208
I_{AR}	Avalanche current (repetitive and non repetitive)	7	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$			250	μA
			$T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 7\text{A}$		1.4	1.68	Ω	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$	3	4	5	V	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		3812		pF
C_{oss}	Output Capacitance			350		
C_{rss}	Reverse Transfer Capacitance			44		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 600\text{V}$ $I_D = 7\text{A}$		145		nC
Q_{gs}	Gate – Source Charge			24		
Q_{gd}	Gate – Drain Charge			70		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 800\text{V}$ $I_D = 7\text{A}$ $R_G = 4.7\Omega$		26		ns
T_r	Rise Time			15		
$T_{d(off)}$	Turn-off Delay Time			85		
T_f	Fall Time			24		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_S	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$			8	A
			$T_c = 80^\circ\text{C}$			6	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -7\text{A}$			1	V	
dv/dt	Peak Diode Recovery ①				25	V/ns	
t_{rr}	Reverse Recovery Time	$I_S = -7\text{A}$ $V_R = 100\text{V}$ $di_S/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$			250	ns
			$T_j = 125^\circ\text{C}$			520	
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		1.12	μC	
			$T_j = 125^\circ\text{C}$		3.03		

 ① dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -7\text{A} \quad di/dt \leq 1000\text{A}/\mu\text{s} \quad V_{DD} \leq 800\text{V} \quad T_j \leq 125^\circ\text{C}$$

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance			0.6	°C/W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight			80		g

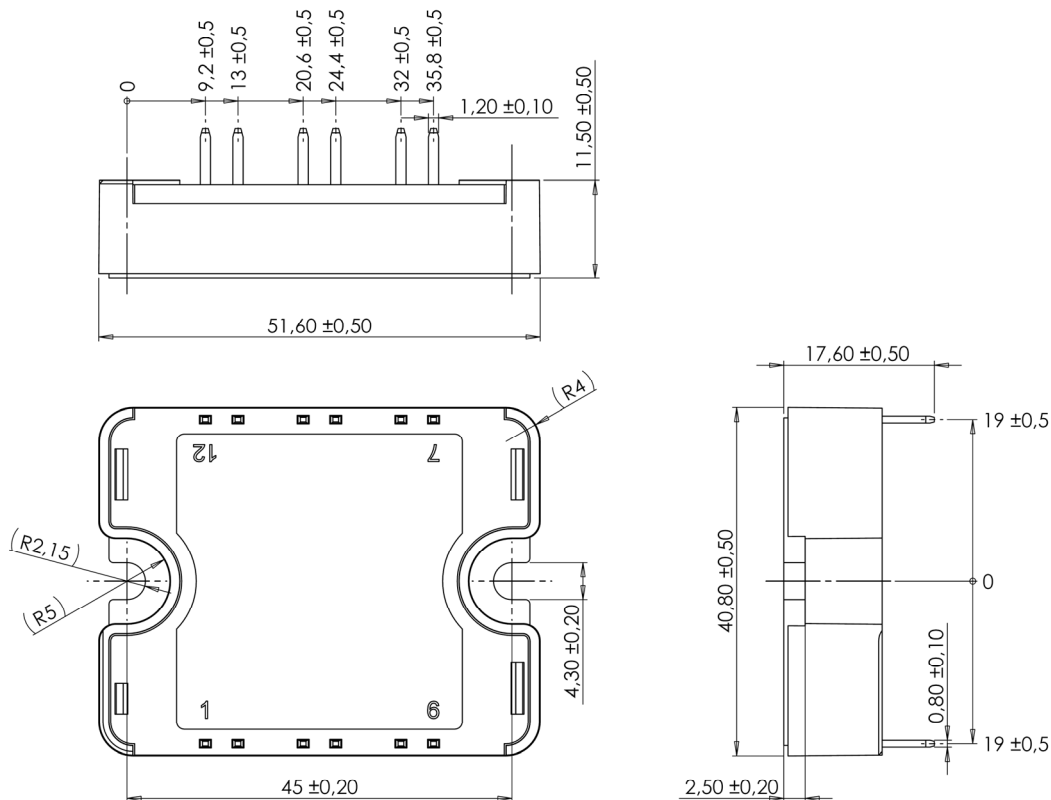
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

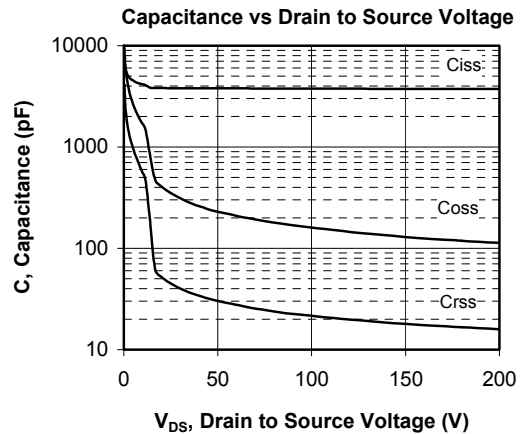
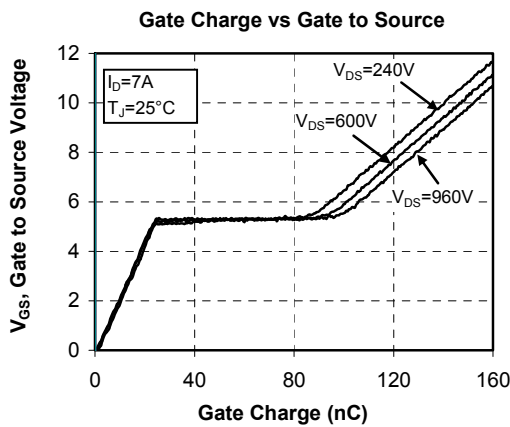
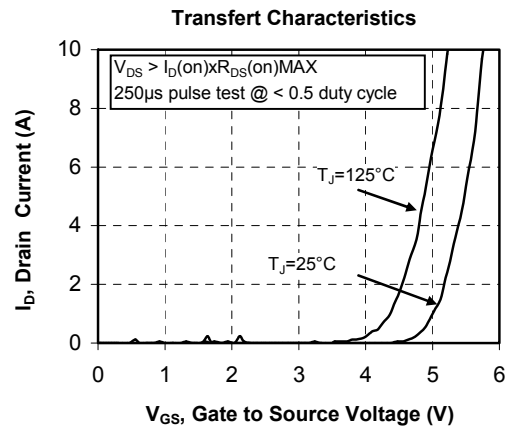
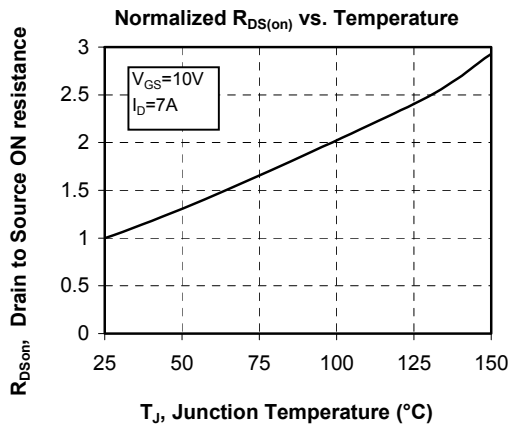
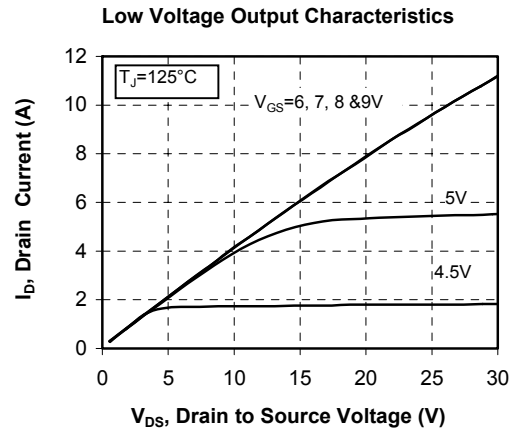
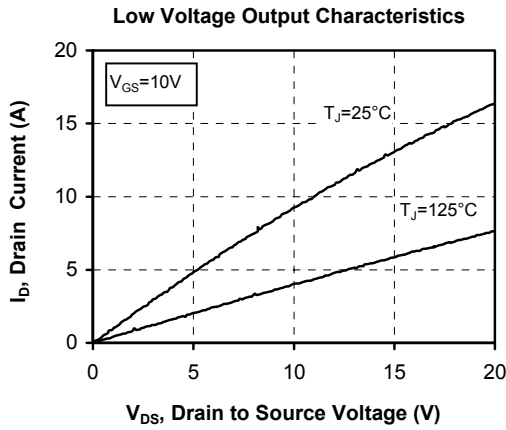
T: Thermistor temperature
 R_T: Thermistor value at T

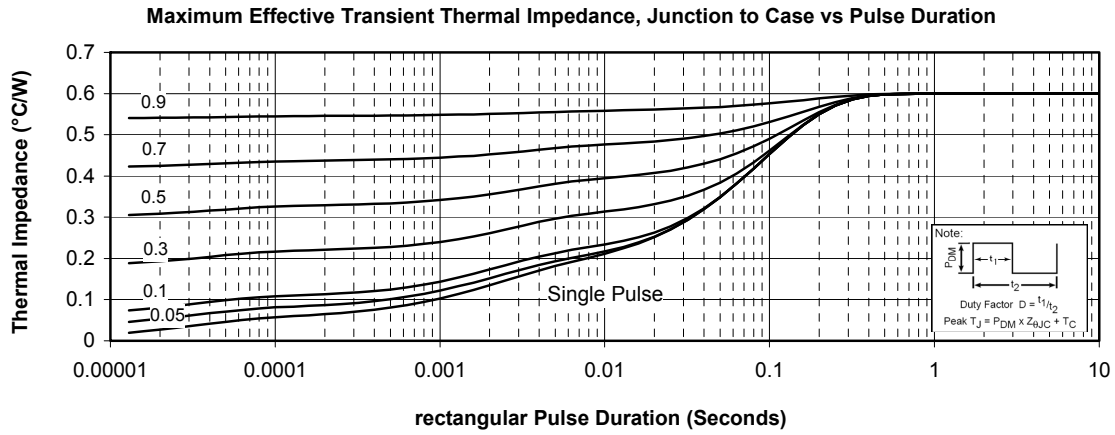
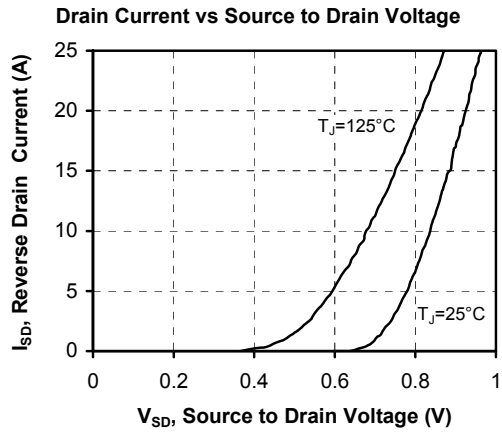
SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Typical Performance Curve





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